

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

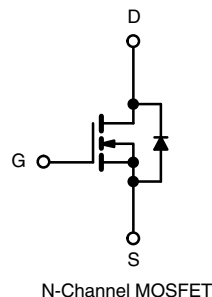
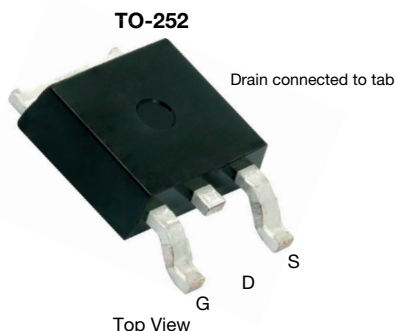
PRODUCT SUMMARY	
V_{DS} (V)	40
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.0036
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.0042
I_D (A)	100
Configuration	Single
Package	TO-252

FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R_g and UIS tested
- AEC-Q101 qualified ^d
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE



ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	$T_C = 25$ °C ^a	I_D	100	A
	$T_C = 125$ °C		80	
Continuous Source Current (Diode Conduction) ^a		I_S	100	
Pulsed Drain Current ^b		I_{DM}	400	
Single Pulse Avalanche Current		I_{AS}	55	mJ
Single Pulse Avalanche Energy		E_{AS}	151	
Maximum Power Dissipation ^b	$T_C = 25$ °C	P_D	136	W
	$T_C = 125$ °C		45	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	50	°C/W
Junction-to-Case (Drain)		R_{thJC}	1.1	

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR4 material).
- Parametric verification ongoing.



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		40	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		1.5	-	2.5	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	50	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A	-	0.0030	0.0036	Ω
		V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0058	
		V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0070	
		V _{GS} = 4.5 V	I _D = 20 A	-	0.0035	0.0042	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 15 A		-	105	-	S
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	4880	5860	pF
Output Capacitance	C _{oss}			-	560	670	
Reverse Transfer Capacitance	C _{rss}			-	250	300	
Total Gate Charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 20 V, I _D = 50 A	-	85	130	nC
Gate-Source Charge ^c	Q _{gs}			-	14	-	
Gate-Drain Charge ^c	Q _{gd}			-	14	-	
Gate Resistance	R _g	f = 1 MHz		0.6	1.5	3	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 20 V, R _L = 0.4 Ω I _D ≅ 50 A, V _{GEN} = 10 V, R _g = 1 Ω		-	9	11	ns
Rise Time ^c	t _r			-	11	14	
Turn-Off Delay Time ^c	t _{d(off)}			-	39	47	
Fall Time ^c	t _f			-	11	14	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	400	A
Forward Voltage	V _{SD}	I _F = 30 A, V _{GS} = 0 V		-	0.9	1.5	V

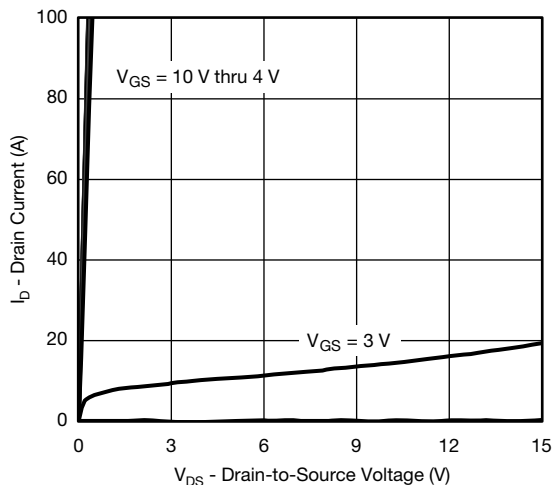
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

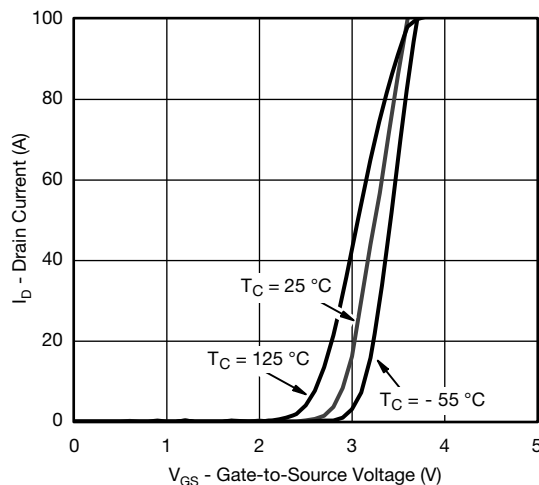
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



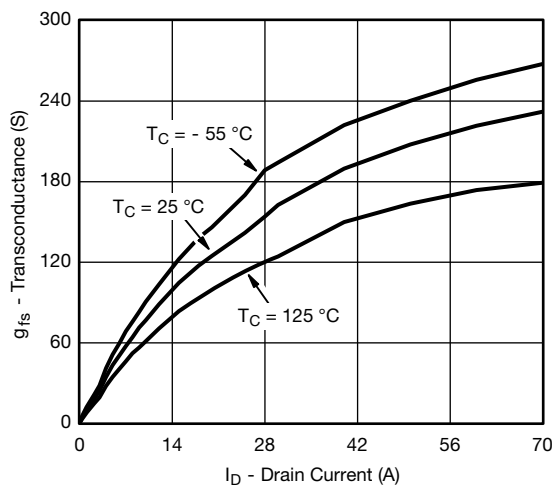
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



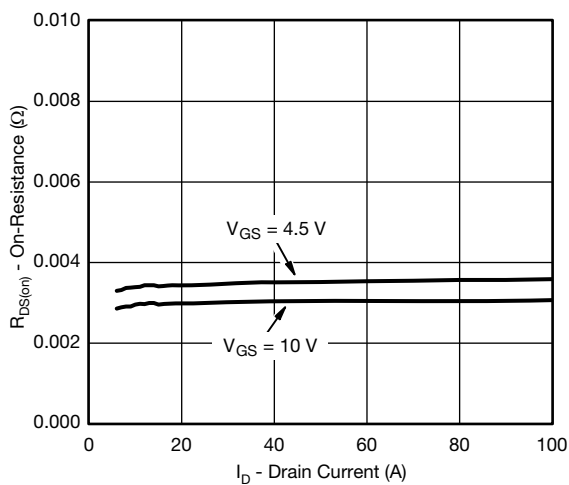
Output Characteristics



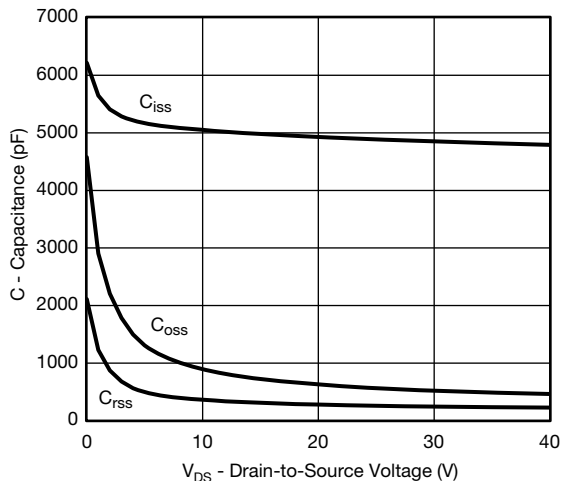
Transfer Characteristics



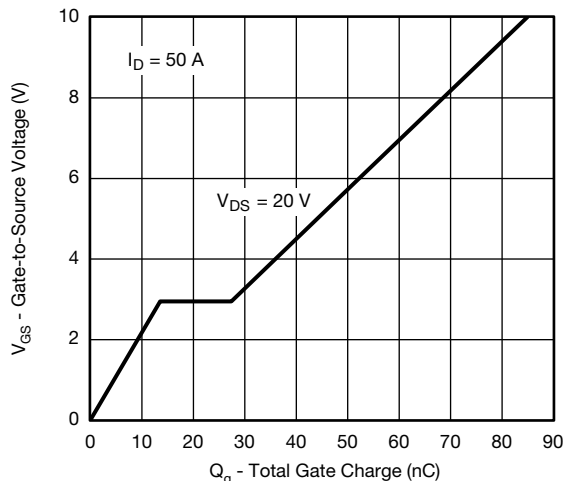
Transconductance



On-Resistance vs. Drain Current



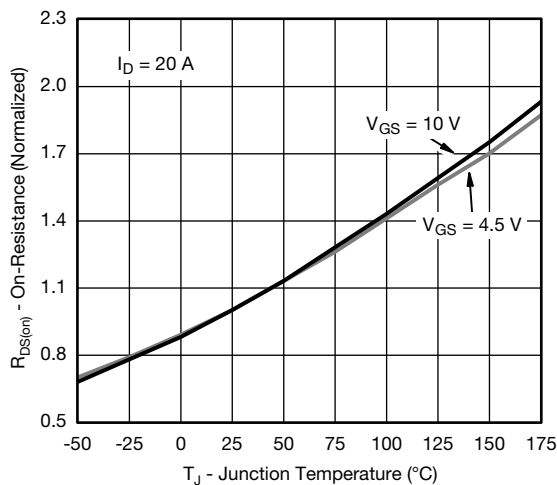
Capacitance



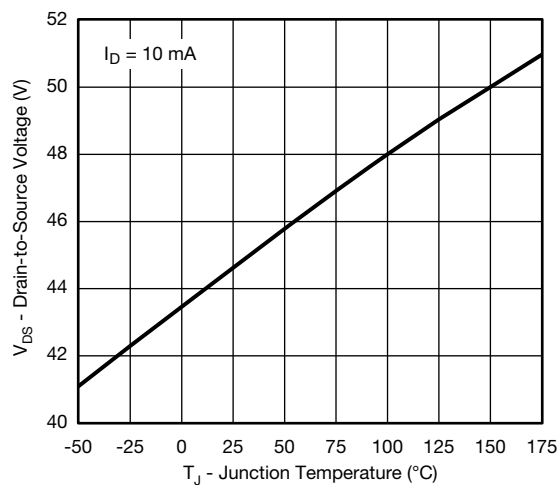
Gate Charge



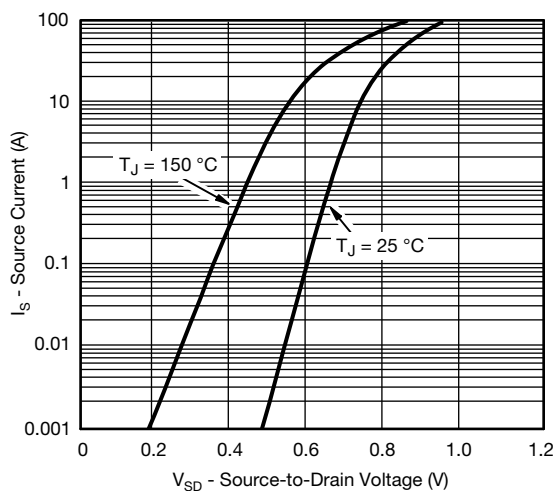
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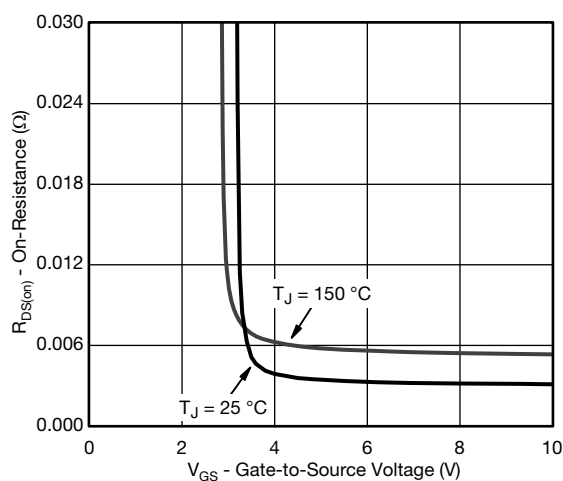
On-Resistance vs. Junction Temperature



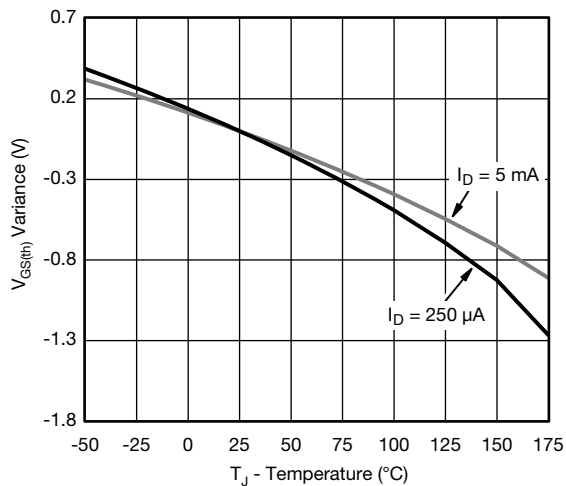
Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage



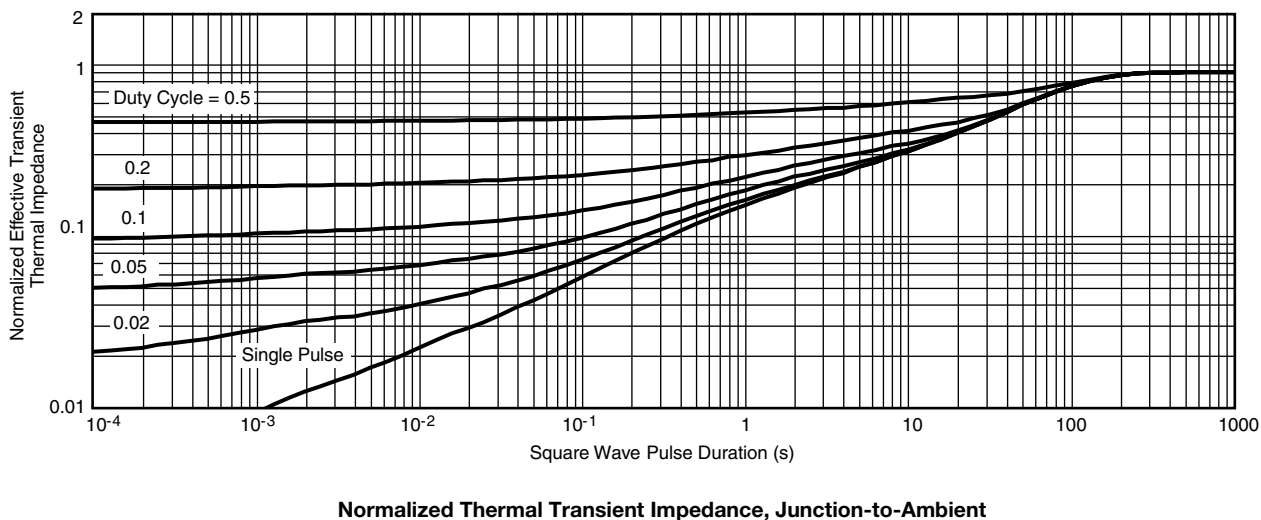
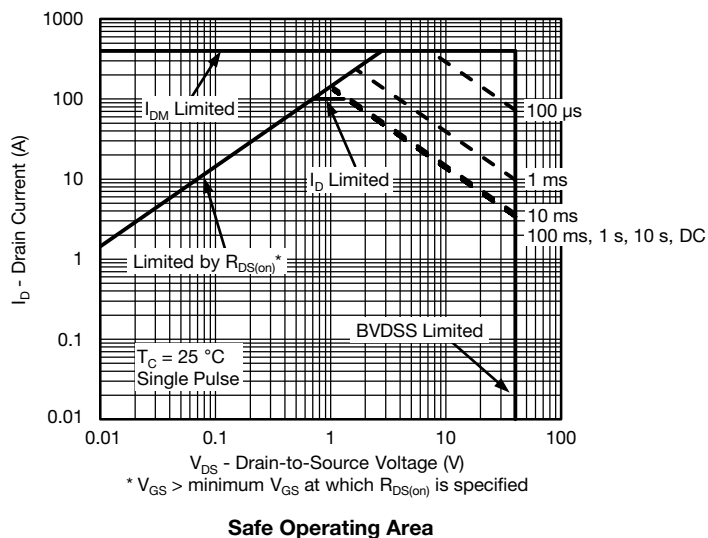
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

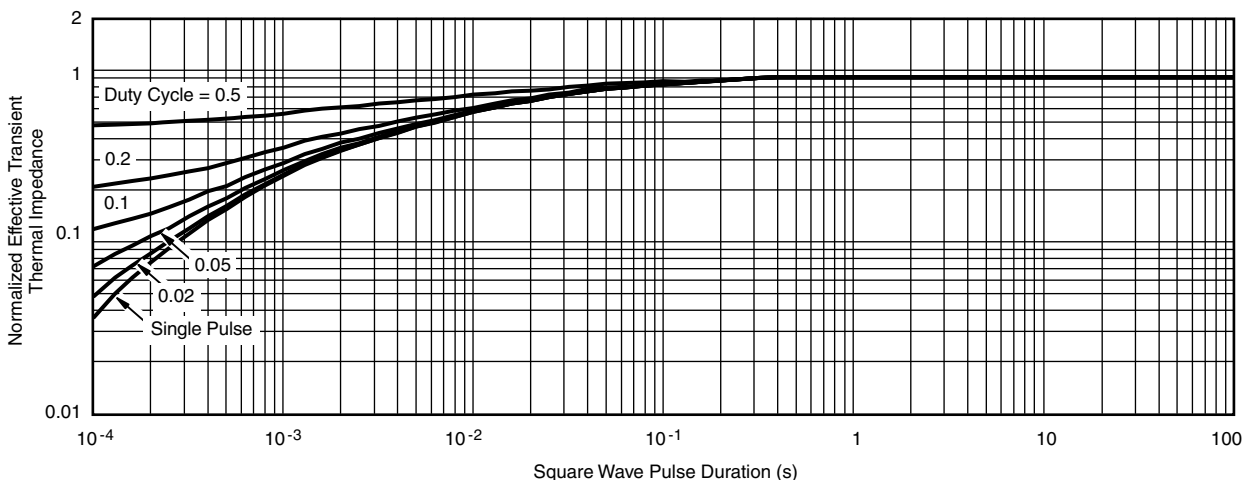


THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)





THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^{\circ}\text{C}$)are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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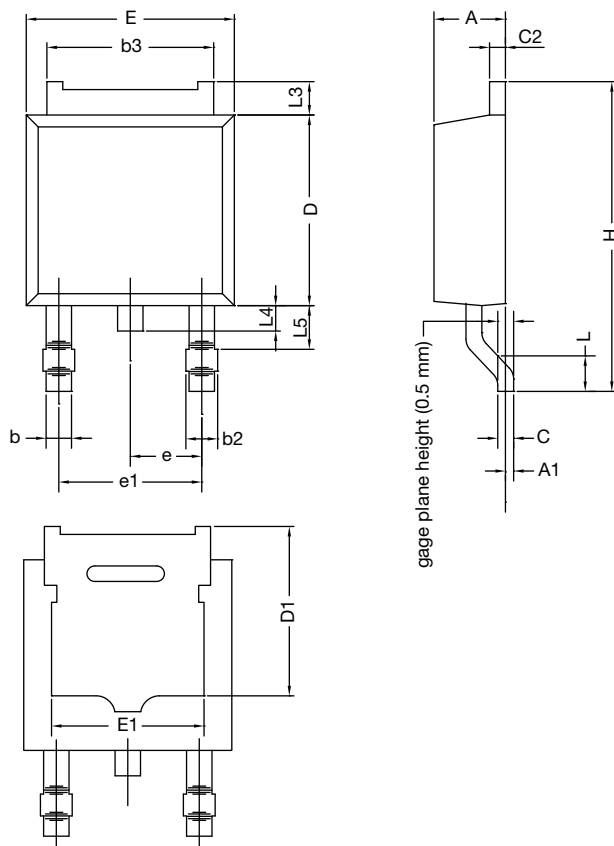
REVISION HISTORY ^a		
REVISION	DATE	DESCRIPTION OF CHANGE
B	04-Aug-15	• Revised R _g minimum limit

Note

a. As of April 2014



TO-252AA Case Outline



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060
ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019				

Note

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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